

SOLAR InOxSide⁺

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Inline junction isolation and rear side smoothing

The InOxSide⁺ combines junction isolation and rear side smoothing as a perfect preparation for a superior surface passivation. The patented single side etching technology ensures powerful smoothing already at low etch depths with lowest cost of ownership. Furthermore, the PreCon and RaPID features offer further flexible configurations for most advanced cell concepts and PID-free cells.

Areas of application

- Rear side smoothing for high efficiency solar cells, e.g. PERC
- Junction isolation and PSG-removal
- Designed for multi- and monocrystalline wafers
- Wafer transfer systems available for automatic loading and unloading

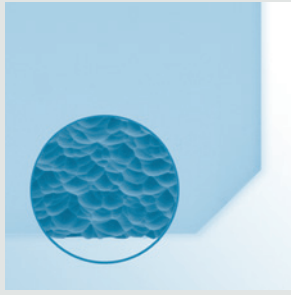
Features and benefits

- Inline single side processing
- Patented process:
 - High quality smoothing
 - Low CoO
- Suited for all relevant passivation layers including AlOx
- Straight line footprint
- Suitable for both multi- and monocrystalline cells

Options

- PreCon: advanced rear side smoothing. The additional PreCon module offers a boost in etch depth to 6 μm for most demanding cell concepts and highest efficiencies.
- RaPID: For PID-free cells. The RaPID module forms a thin oxide on the wafer surface prior to AR deposition - a key factor for the production of PID-free cells. Integrated within the InOxSide[®] tool, the RaPID module does not increase the equipment footprint.





Smooth
rear side

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Front view InOxSide+

Technical Data InOxSide+

Platform	NIAK 2, 5 lanes
Process	Junction isolation + PSG-removal + rear side smoothing
Dimensions	7800 x 2150 x 2350 mm (length x width x height)
Throughput	5000 wafers/h gross
Wafer thickness	> 150 μm
Wafer size	156-161 mm, square and pseudo-square
Etch depth	1.0 - 4.0 μm

RENA V50001